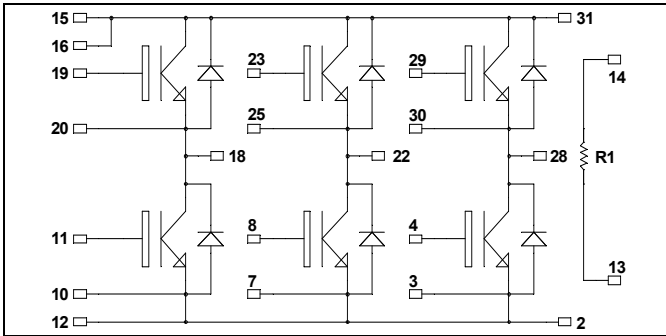


## 3 Phase bridge NPT IGBT Power Module

**$V_{CES} = 1200V$**   
 **$I_C = 25A @ T_c = 80^\circ C$**



It is recommended to connect a decoupling capacitor between pins 31 & 2 to reduce switching overvoltages, if DC Power is connected between pins 15, 16 & 12. Pins 15 & 16 must be shorted together.

### Application

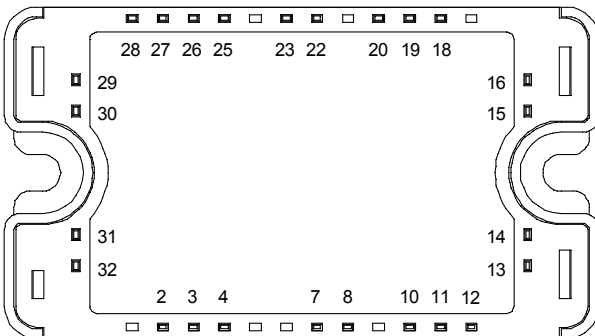
- Motor control

### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant



### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	40
		$T_C = 80^\circ C$	25
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	100
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	208
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	50A@1150V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$	$T_j = 25^\circ\text{C}$		250	$\mu\text{A}$	
			$T_j = 125^\circ\text{C}$		500		
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 25\text{A}$	$T_j = 25^\circ\text{C}$	2.5	3.2	3.7	V
			$T_j = 125^\circ\text{C}$		4.0		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1\text{mA}$	4		6	V	
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA	

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0\text{V}$ $V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		1650		pF
$C_{oes}$	Output Capacitance			250		
$C_{res}$	Reverse Transfer Capacitance			110		
$Q_g$	Total gate Charge	$V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 25\text{A}$		160		nC
$Q_{ge}$	Gate – Emitter Charge			10		
$Q_{gc}$	Gate – Collector Charge			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 25\text{A}$ $R_G = 22\Omega$		60		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			305		
$T_f$	Fall Time			30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 25\text{A}$ $R_G = 22\Omega$		60		ns
$T_r$	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			346		
$T_f$	Fall Time			40		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = 15\text{V}$ $V_{Bus} = 400\text{V}$ $I_C = 25\text{A}$ $R_G = 22\Omega$	$T_j = 125^\circ\text{C}$		3.5	mJ
$E_{off}$	Turn-off Switching Energy		$T_j = 125^\circ\text{C}$		1.5	

**Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$		100	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		500	
$I_F$	DC Forward Current			30		A
$V_F$	Diode Forward Voltage	$I_F = 30\text{A}$		2.6	3.1	V
		$I_F = 60\text{A}$		3.2		
		$I_F = 30\text{A}$	$T_j = 125^\circ\text{C}$		1.8	
$t_{rr}$	Reverse Recovery Time	$I_F = 30\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		300	ns
			$T_j = 125^\circ\text{C}$		380	
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		360	nC
			$T_j = 125^\circ\text{C}$		1700	

**Temperature sensor NTC** (see application note APT0406 on [www.microsemi.com](http://www.microsemi.com) for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

### Thermal and package characteristics

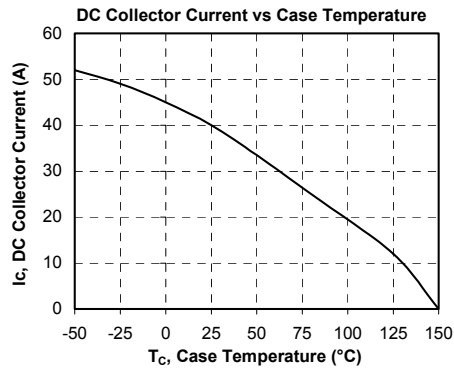
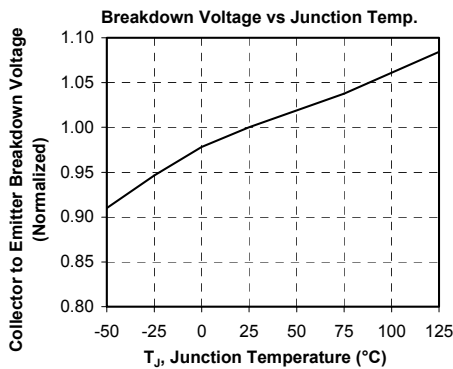
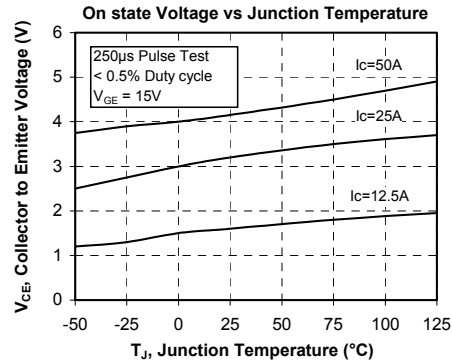
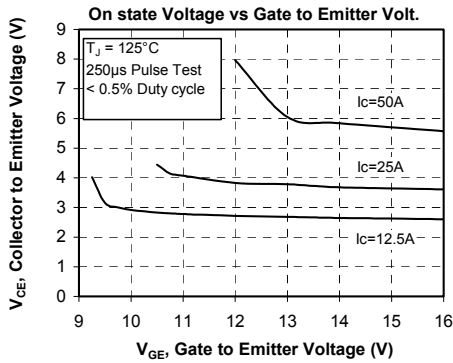
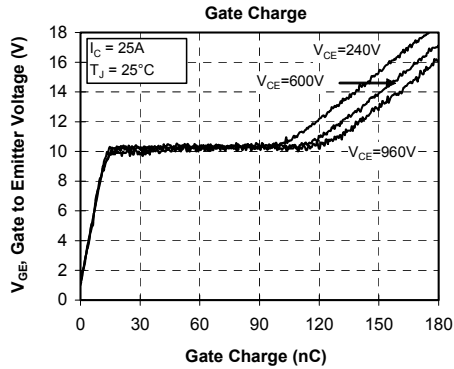
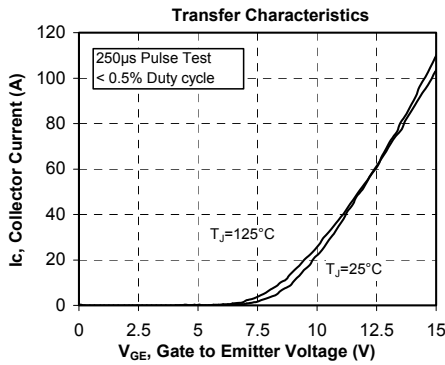
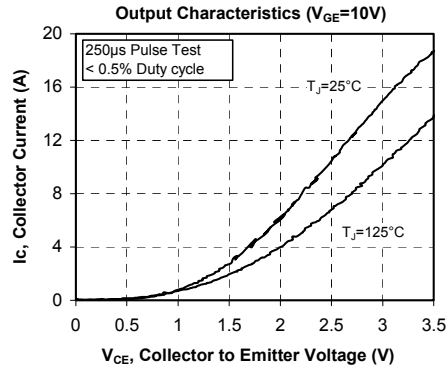
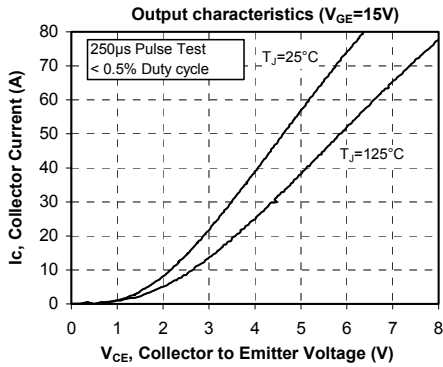
Symbol	Characteristic	Min	Typ	Max	Unit		
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.6	°C/W		
		Diode		1.2			
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz	2500			V		
T <sub>J</sub>	Operating junction temperature range	-40		150	°C		
T <sub>STG</sub>	Storage Temperature Range	-40		125			
T <sub>C</sub>	Operating Case Temperature	-40		100			
Torque	Mounting torque		To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight					110	g

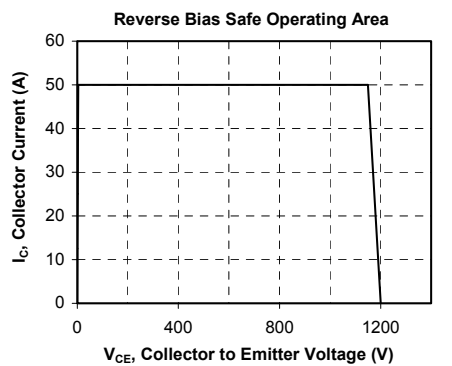
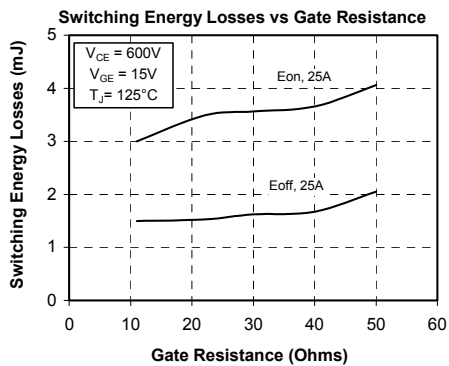
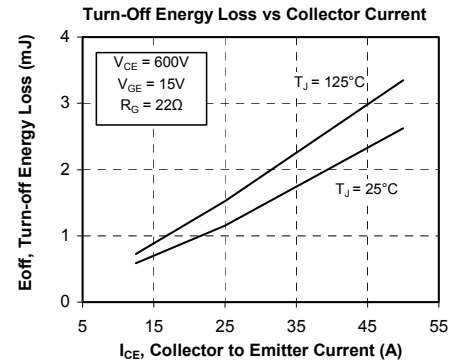
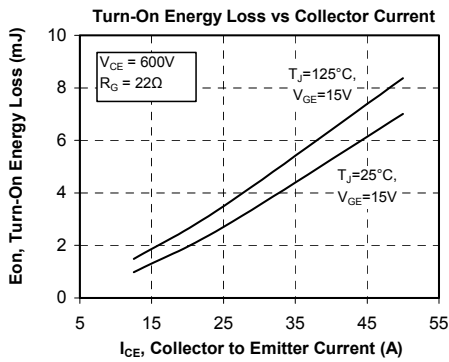
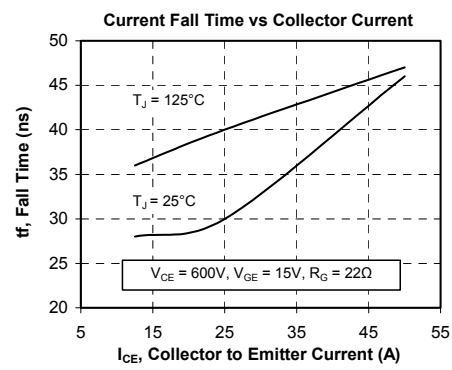
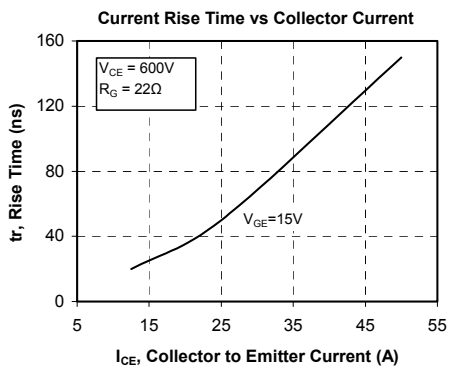
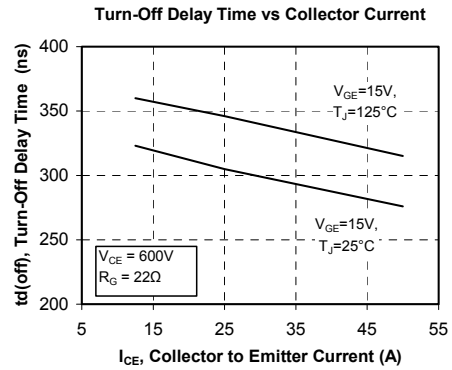
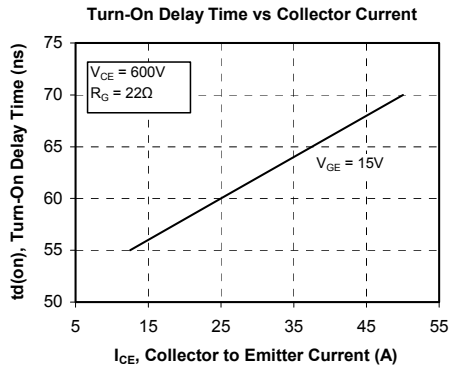
### SP3 Package outline (dimensions in mm)

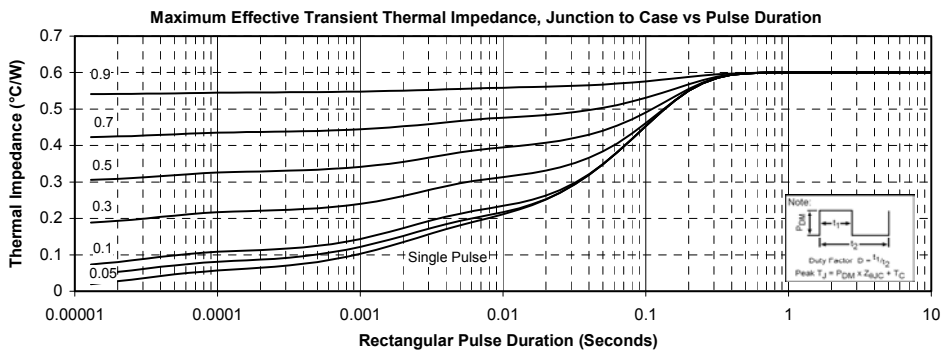
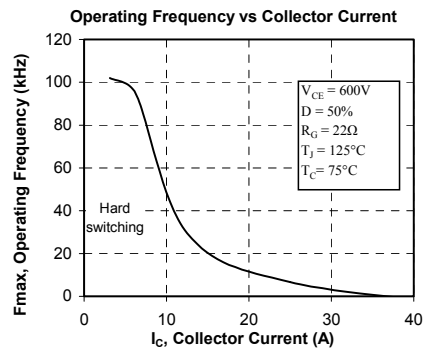
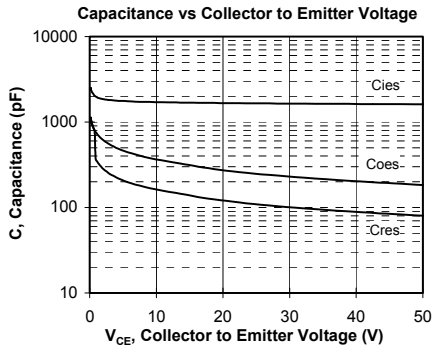


See application note 1901 - Mounting Instructions for SP3 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve







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